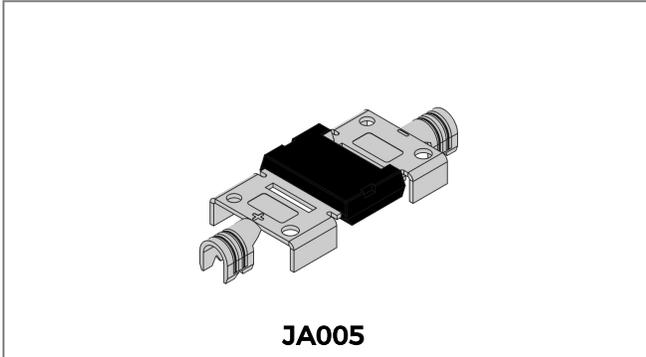


## GFJ3545TS Power Schottky Module Bypass Diode



### Features

- Trench MOS Schottky technology
- Low thermal resistance
- Lower forward voltage drop, low power loss
- Isolate Package design, ideal for heat dispersion
- High forward current capability
- Excellent anti-humidity
- Low profile package
- High forward surge capability
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

### Mechanical Data

- Case: JA005
- High temperature soldering guaranteed
- Heated-tool welding 260°C, 10 seconds
- Marking Code: GFJ3545TS

### Maximum Ratings (limiting values, at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	-	45	V
Average Rectified Forward Current	$I_{F(AV)}$	$T_C = 123^\circ\text{C}$ , In DC	35	A
Peak One Cycle Non-Repetitive Surge Current	$I_{FSM}$	8.3 ms, half Sine pulse, $T_J = 25^\circ\text{C}$	350	A
Rating for fusing ( $t < 8.3\text{ms}$ )	$I^2t$	$T_J = 25^\circ\text{C}$	500	A <sup>2</sup> sec

### Electrical Characteristics

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	$V_{F1}$	@ 35A, Pulse, $T_J = 25^\circ\text{C}$	0.48	0.52	V
Reverse Current*	$I_{R1}$	@ $V_R = \text{rated } V_R$ , $T_J = 25^\circ\text{C}$	0.03	0.20	mA
	$I_{R2}$	@ $V_R = \text{rated } V_R$ , $T_J = 100^\circ\text{C}$	-	12	mA
	$I_{R3}$	@ $V_R = \text{rated } V_R$ , $T_J = 125^\circ\text{C}$	20	55	mA
Junction Capacitance	$C_T$	@ $V_R = 5\text{V}$ , $T_C = 25^\circ\text{C}$ $f_{SIC} = 1\text{MHz}$	5000	-	pF

\* Pulse width < 300  $\mu\text{s}$ , duty cycle < 2%

**Thermal-Mechanical Specifications(Ta=25°C Unless otherwise specified)**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	IN DC Forward Mode, without reverse bias, $t \leq 1$ h	-55 to +200	°C
Storage Temperature	$T_{stg}$	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	-	1.0	°C/W

**Ratings and Characteristics Curves**

Figure1 Typical Forward Characteristics

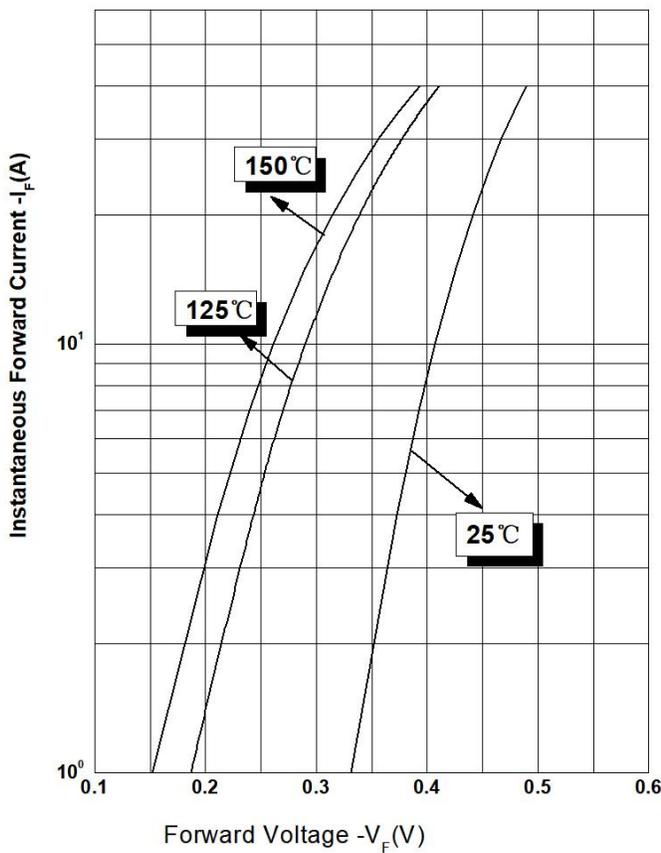


Figure 2 Typical Reverse Characteristics

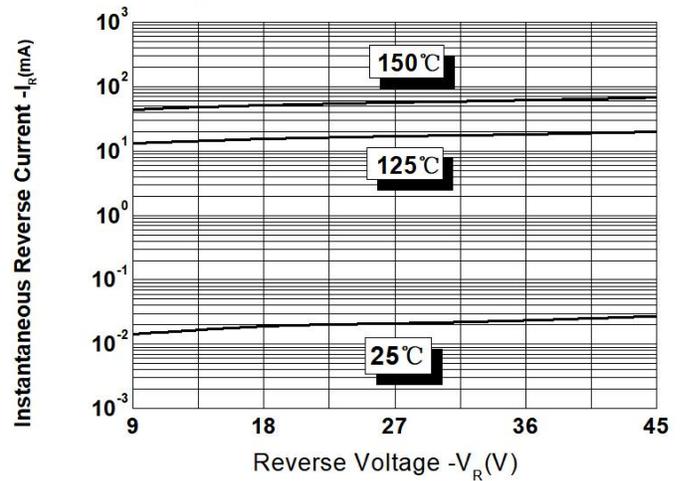
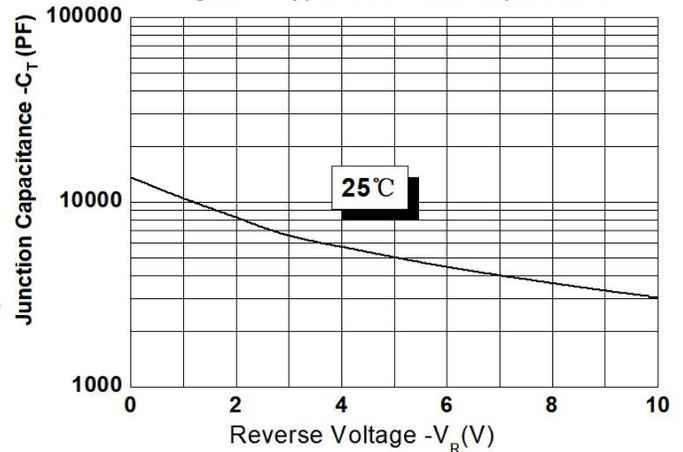


Figure 3 Typical Junction Capacitance

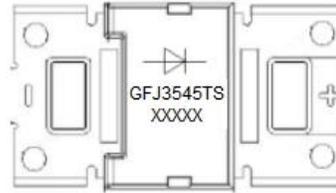


Technical Data  
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**Ordering Information**

Device	Package	Shipping
GFJ3545TS	JA005	30pcs/Tube

**Marking Diagram**



Where XXXXX is YYWWL  
 GFJ3545TS = Device Code  
 YY = Year  
 WW = Week  
 L = Lot Number

Order P/N	Terminals	Additional
GFJ3545TS-S1	Tin Plated	None
GFJ3545TS-S2	Tin Plated	Solder Paste
GFJ3545TS-S3	Tin Plated	Solder Block



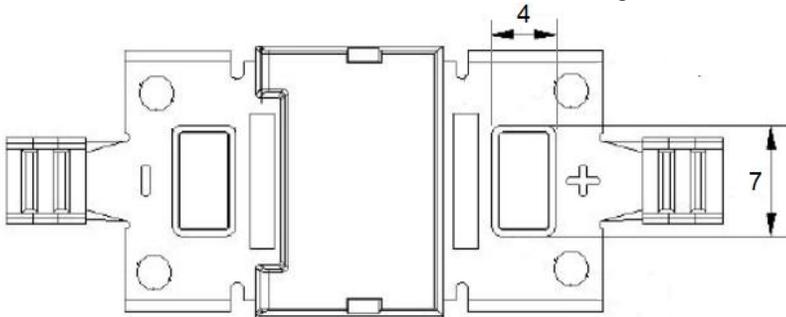
Solder Paste



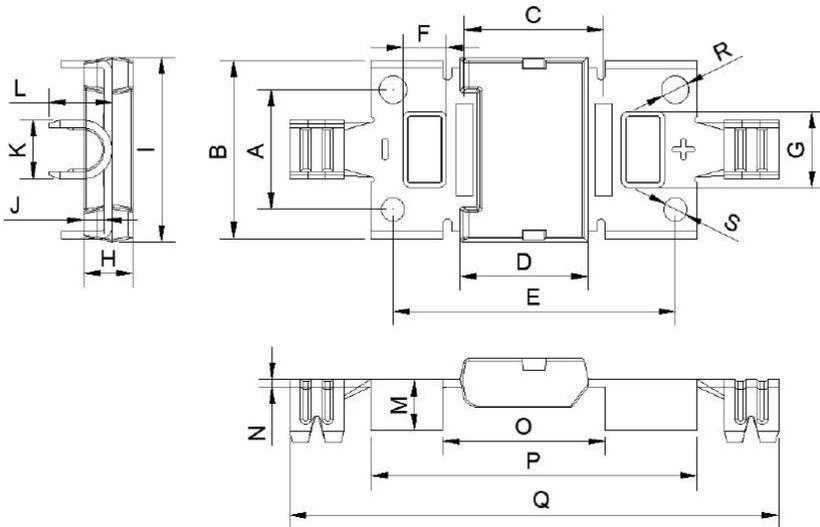
Solder Block

**Solder block Specification**

The composition of the tin block is Sn50Pb50 with flux.  
 The size of the tin block is  $6(\pm 0.15) \times 3.5(\pm 0.15) \times 1(\pm 0.08)$  mm.  
 The composition and size of tin blocks can be customized according to customer requirements.  
 Solder block to be centered, not exceed the flat groove.



**Mechanical Dimensions JA005 (Millimeters)**



Symbol	Dimensions in millimeters	
	Min.	Max
A	10.5	11.5
B	15.9	16.9
C	12.6	13
D	11.23	12.23
E	25.5	26.5
F	3.5	4.5
G	6.5	7.5
H	4.3	4.7
I	16.5	17.5
J	1.7	2.1
K	5	5.8
L	5.6	6
M	4.4	5
N	0.6	0.8
O	14.73	15.13
P	29.5	30.5
Q	44.5	45.5
R	2.35	2.65
S	2	2.3

**Technical Data**

**Data Sheet N2921 REV.-**

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